

Inventor: Janos Fucsko et al.

Title: Methods of Etching Silicon Nitride Substantially Selectively Relative to an Oxide of Aluminum and Methods of Forming Trench Isolation Within a Semiconductor Substrate

Assignee: Micron Technology, Inc.

**INFORMATION DISCLOSURE STATEMENT**


References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR § 1.56. Copies of the cited art are included. No admission is made regarding whether all the submitted references are prior art.

Respectfully submitted,

Dated: 18 Sep 2003

Attorney: \_\_\_\_\_

  
James E. Lake  
Reg. No. 44,854

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2271		SERIAL NO. Unknown	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: Janos Fucsko et al.			
				FILING DATE Filed Herewith		GROUP Unknown	

U.S. PATENT DOCUMENTS							
*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
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FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AJ							
	AK							
	AL							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
	AM		Deckert, <i>Pattern Etching of CVD Si<sub>3</sub>N<sub>4</sub>/SiO<sub>2</sub> Composites in HF/Glycerol Mixtures</i> ,
			127 J. ELECTROCHEM. SOC., No. 11, pp. 2433-2438 (November 1980).
	AN		
	AO		

EXAMINER	DATE CONSIDERED
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.